42mΩ, 650V, Super Junction N-Channel Power MOSFET SRC65R042B

General Description

The Sanrise SRC65R042B is a high voltage power MOSFET, fabricated using advanced super junction technology. The resulting device has extremely low on resistance, low gate charge and fast switching time, making it especially suitable for applications which require superior power density and outstanding efficiency.

The SRC65R042B break down voltage is 650V and it has a high rugged avalanche characteristics. The SRC65R042B is available in TO-247 package.

Features

- Ultra Low $R_{DS(ON)}$ = 42mΩ @ V_{GS} = 10V.
- Ultra Low Gate Charge, Qg=182nC typ.
- Intrinsic Fast-Recovery Body Diode
- Fast switching capability
- Robust design with better EAS performance
- Non-automotive Qualified

Application

- AC/DC Power Supply
- EV Charger
- Server / Telecom
- Solar Inverter

Symbol

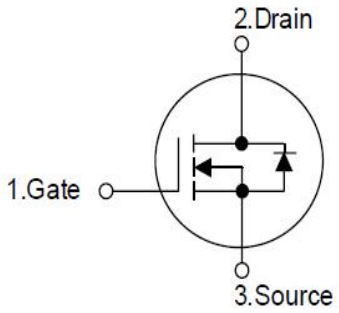
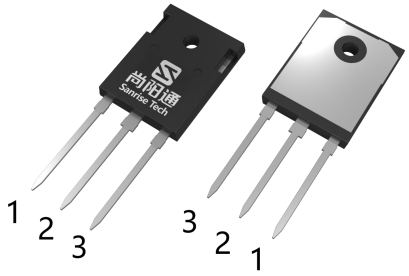


Figure 1 Symbol of SRC65R042B

Package Type



TO-247

Figure 2 Package Type of SRC65R042B

Ordering Information

SRC65R042B□□–□

- Circuit Type
- Package
  T: TO-247
- E: Lead Free
  G: Green
- Blank: Tube

Package	Part Number	Marking ID	Packing Type
TO-247	SRC65R042BT-G	SRC65R042BTG	Tube

42mΩ, 650V, Super Junction N-Channel Power MOSFET SRC65R042B

Absolute Maximum Ratings

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage (static)		V_{GSS}	±20	V
Gate-Source Voltage (dynamic)，AC (f>1Hz)		V_{GSS}	±30	V
Power Dissipation（Tc=25℃,TO-247）		P_{tot}	520	W
Continuous Drain Current	T_C=25ºC	I_D	78	A
	T_C=100ºC		49.2	
	T_C=125ºC		34.8	
Pulsed Drain Current (Note 2)		I_{DM}	234	A
Avalanche Energy, Single Pulse (Note 3)		E_{AS}	870	mJ
Avalanche Energy, Repetitive (Note 2)		E_{AR}	0.9	mJ
Avalanche Current, Repetitive (Note 2)		I_{AR}	6.6	A
Continuous Diode Forward Current		I_S	78	A
Diode Pulse Current		$I_{S.PULSE}$	234	A
MOSFET dv/dt Ruggedness, V_{DS}<=480V		dv/dt	50	V/ns
Reverse Diode dv/dt, V_{DS}<=480V, I_{SD}<=I_D		dv/dt	50	V/ns
Operating Junction Temperature		T_J	150	ºC
Storage Temperature		T_{STG}	-55 to 150	ºC
Lead Temperature (Soldering, 10 sec)		T_{LEAD}	260	ºC

Note:

1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. I_{AS} = 6.6A, V_{DD} =120V, R_G = 25Ω, Starting T_J = 25°C

Parameter		Symbol	Min	Typ	Max	Unit
Thermal resistance, Junction-to-Case	TO-247	R_{thJC}			0.24	ºC /W
Thermal resistance, Junction-to-Ambient	TO-247	R_{thJA}			54	ºC /W

Electrical Characteristics

T_J = 25℃, unless otherwise specified.

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250uA	650			V
Zero Gate Voltage Drain Current		I_{DSS}	V_{DS}=650V, V_{GS}=0V			10	uA
Gate-Body Leakage Current	Forward	I_{GSSF}	V_{GS}=20V, V_{DS}=0V			100	nA
	Reverse	I_{GSSR}	V_{GS}=-20V, V_{DS}=0V			-100	nA
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=1.6mA	3.2	4.0	4.8	V
Static Drain-Source On-Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=30A		35	42	mΩ
Gate Resistance		R_G	f=1MHz, Open Drain		0.7		Ω
Dynamic Characteristics							
Input Capacitance		C_{ISS}	V_{DS}=50V, V_{GS}=0V, f=1MHz		7200		pF
Output Capacitance		C_{OSS}			281.4		
Reverse Transfer Capacitance		C_{RSS}			4.7		
Effective output capacitance, energy related NOTE5		$C_{O(er)}$	V_{GS}=0V, V_{DS}=0…400V		155.1		pF
Effective output capacitance, time related NOTE6		$C_{O(tr)}$			905.9		
Turn-on Delay Time		$t_{d(on)}$	V_{DD}=400V, I_D=38A R_G=3.3Ω, V_{GS}=10V		17		ns
Rise Time		t_r			6.6		
Turn-off Delay Time		$t_{d(off)}$			112		
Fall Time		t_f			4.3		
Gate Charge Characteristics							
Gate to Source Charge		Q_{gs}	V_{DD}=480V, I_D=38A V_{GS}=0 to 10V		46.3		nC
Gate to Drain Charge		Q_{gd}			92.2		
Gate Charge Total		Q_g			182		
Gate Plateau Voltage		$V_{plateau}$			6.5		V
Reverse Diode Characteristics							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS}=0V, I_{SD}=38A		0.9	1.1	V
Reverse Recovery Time		t_{rr}	V_R=100V, I_F=38A dI$_F$/dt=100A/us		168		ns
Reverse Recovery Charge		Q_{rr}			1.17		uC
Peak Reverse Recovery Current		I_{rrm}			14.0		A

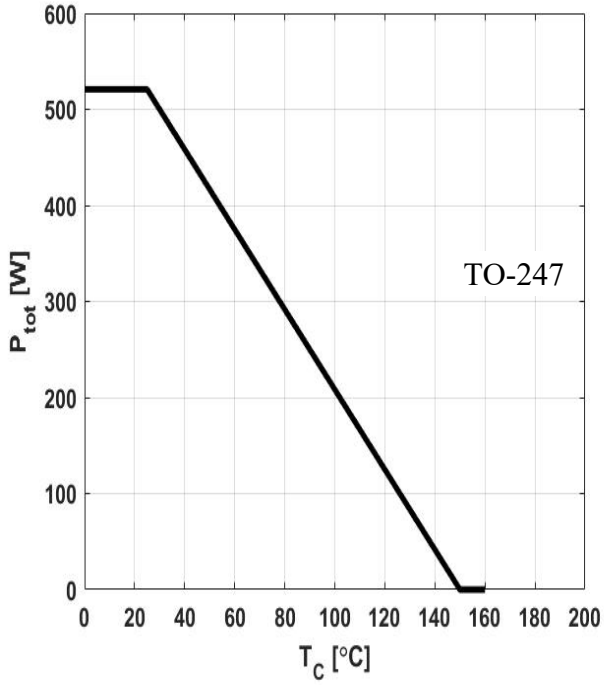
Note:

5. $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 480V

6. $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 480 V

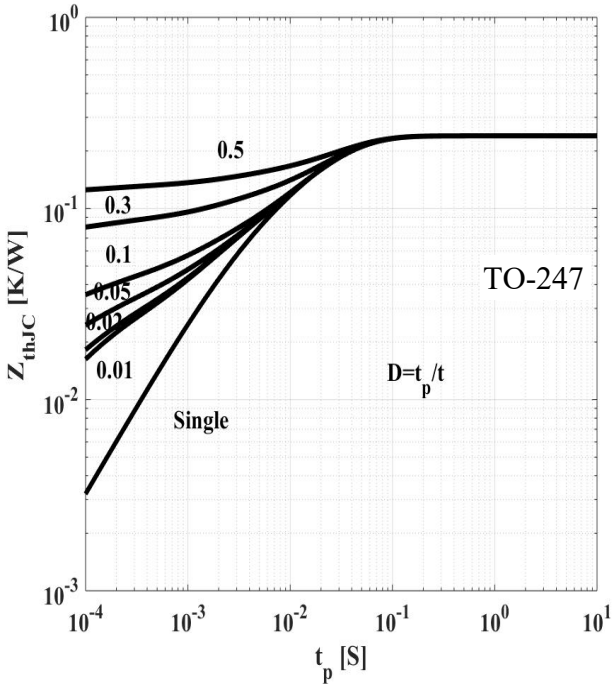
Typical Performance Characteristics

Figure 3: Power Dissipation



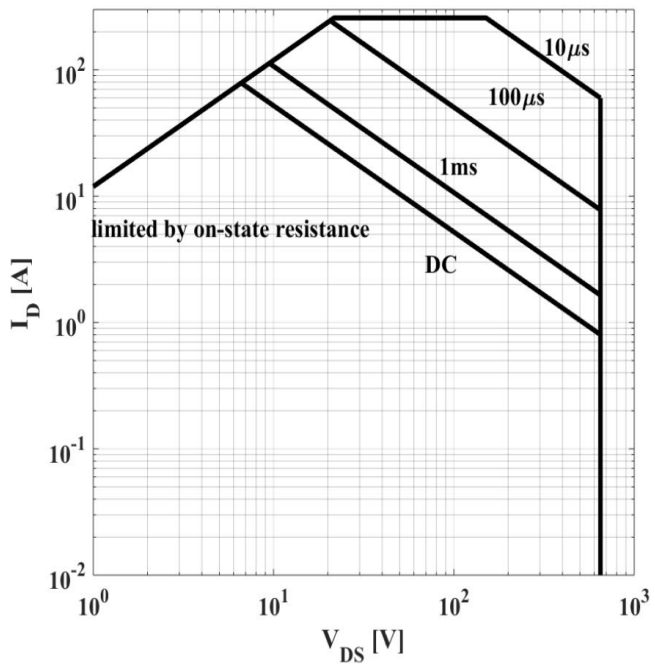
$P_{tot} = f(T_c)$

Figure 4: Max. Transient Thermal Impedance



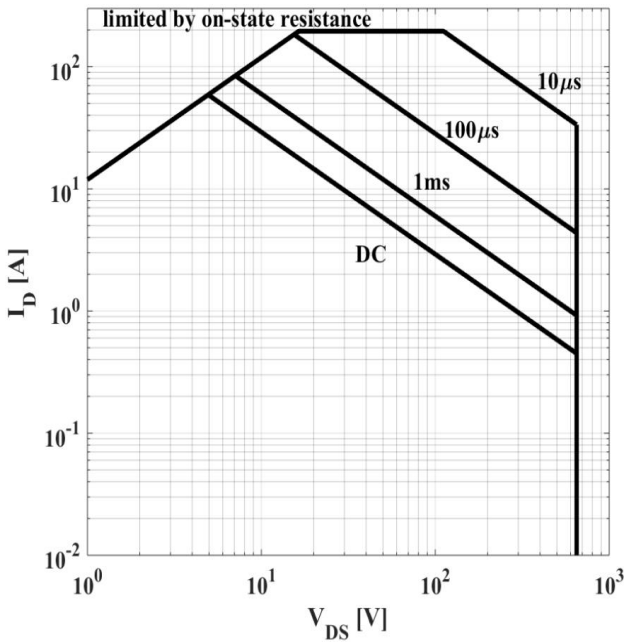
$Z_{(thJC)} = f(t_p)$; parameter: $D = t_p/T$

Figure 5: Safe Operating Area



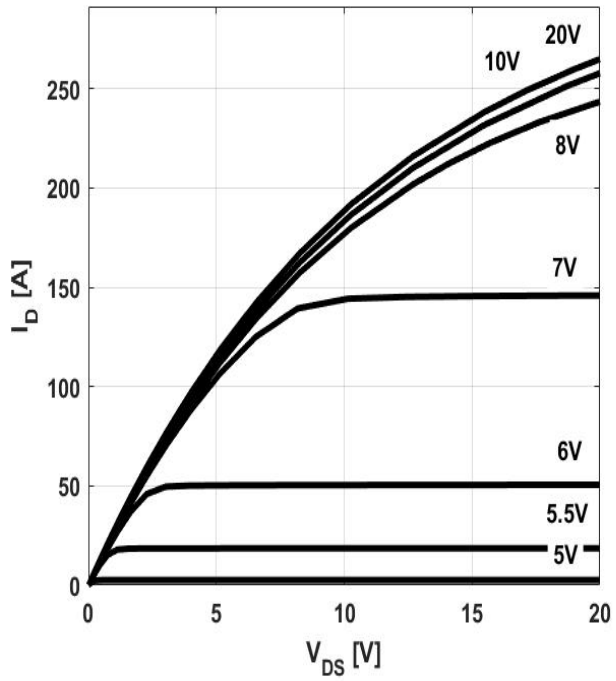
$I_D = f(V_{DS})$; T_c= 25ºC; V_{GS}>7V; parameter t_p

Figure 6: Safe Operating Area



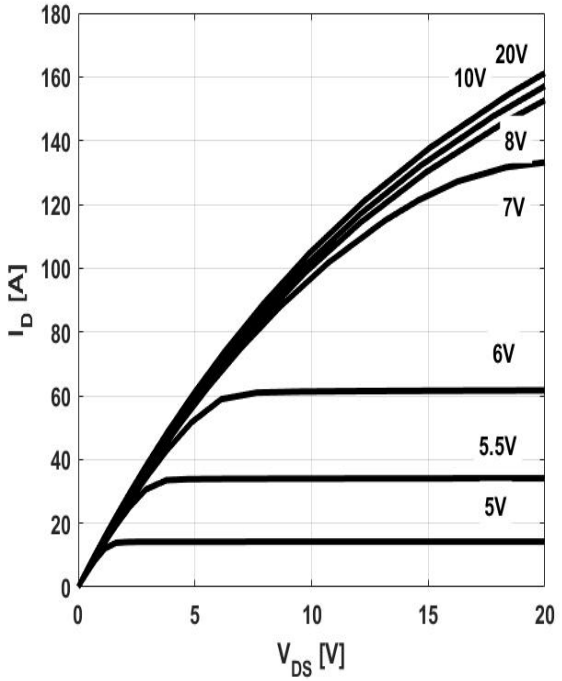
$I_D = f(V_{DS})$; T_c= 80ºC; V_{GS}>7V; parameter t_p

Figure 7: Typ. Output Characteristics



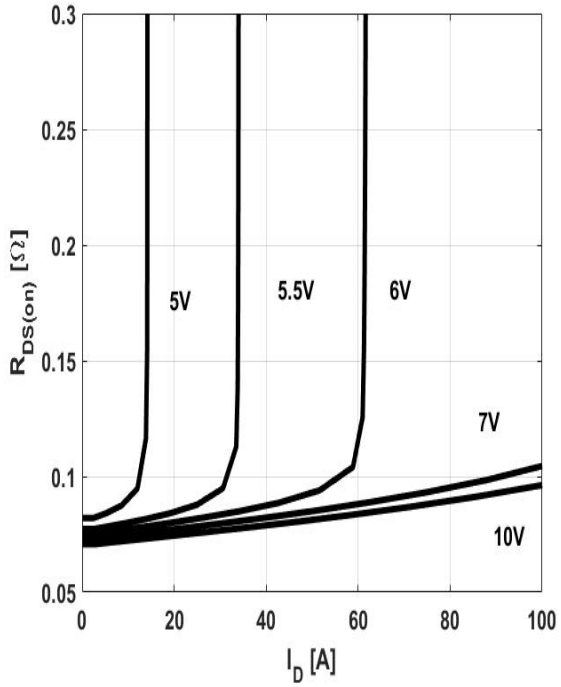
$I_D = f(V_{DS})$; Tj= 25ºC; parameter: V_{GS}

Figure 8: Typ. Output Characteristics



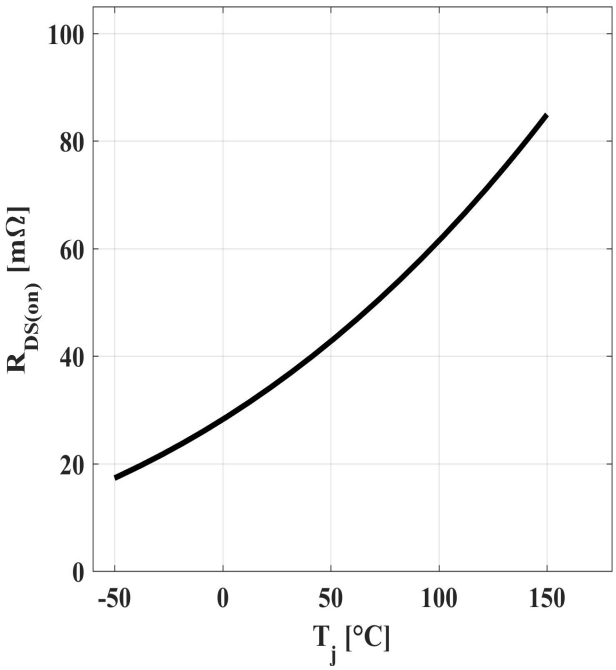
$I_D = f(V_{DS})$; T_j= 125ºC; parameter: V_{GS}

Figure 9: Typ. Drain-Source On-State Resistance



$R_{DS(ON)} = f(I_D)$; T_j=125ºC; parameter: V_{GS}

Figure 10: Typ. Drain-Source On-State Resistance



$R_{DS(ON)} = f(T_j)$; I_D=38A; V_{GS}=10V

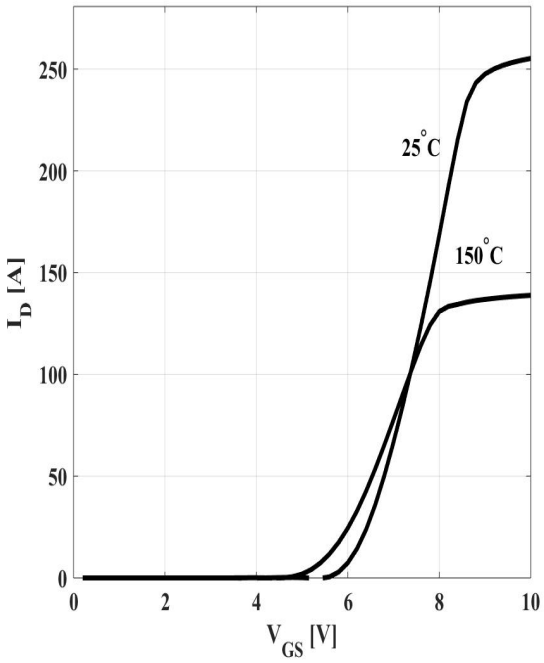
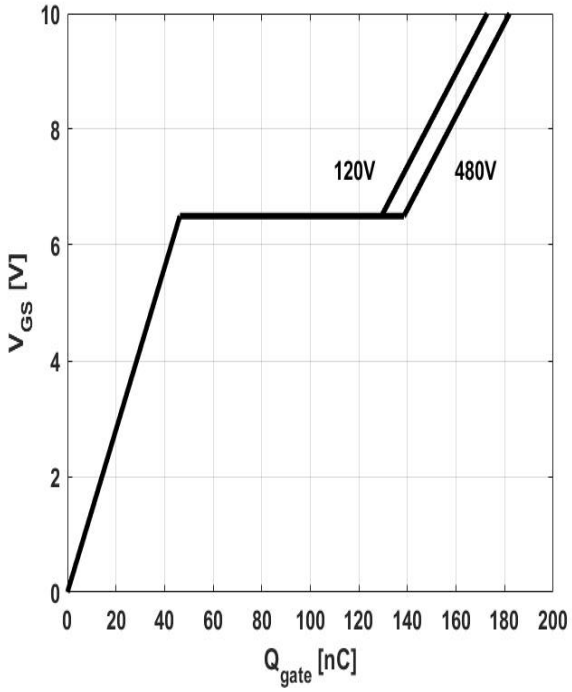
Figure 11: Typ. Transfer Characteristics	Figure 12: Typ. Gate Charge
	
$I_D = f(V_{GS})$; $V_{DS} = 20V$	$V_{GS} = f(Q_{gate})$, $I_D = 38A$ pulsed

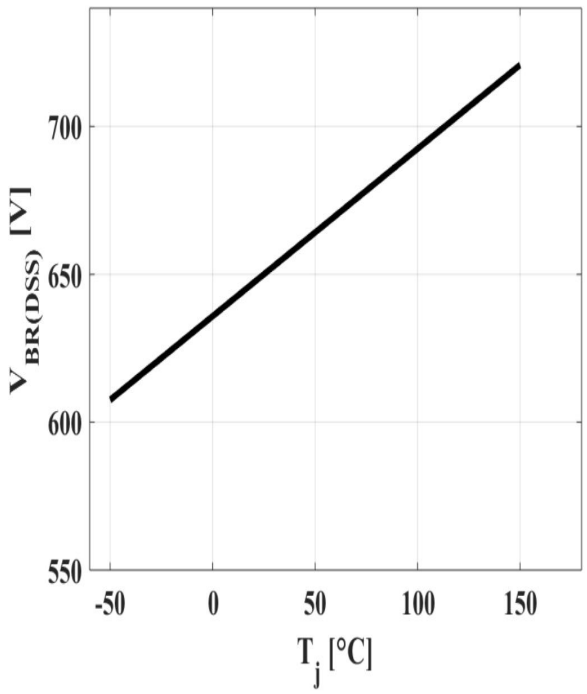
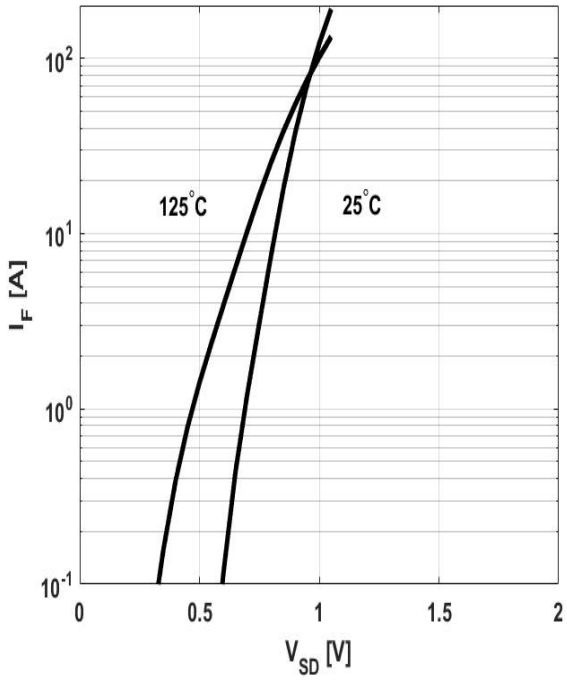
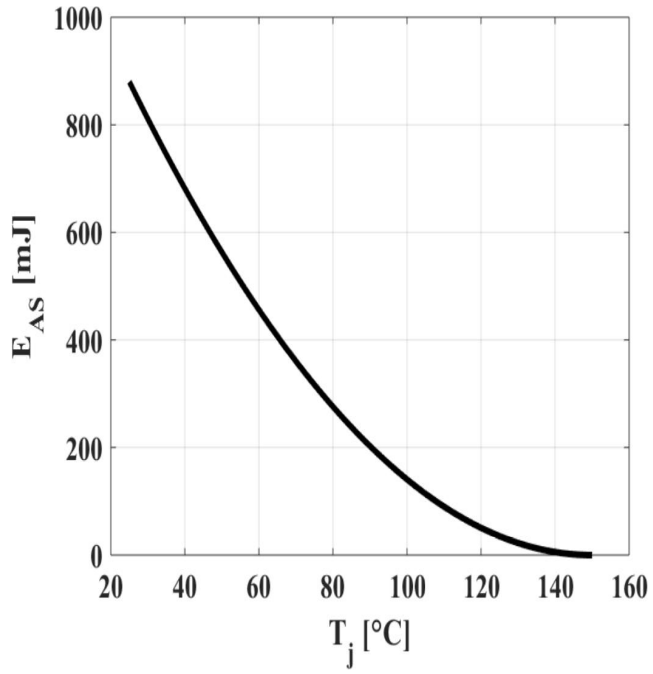
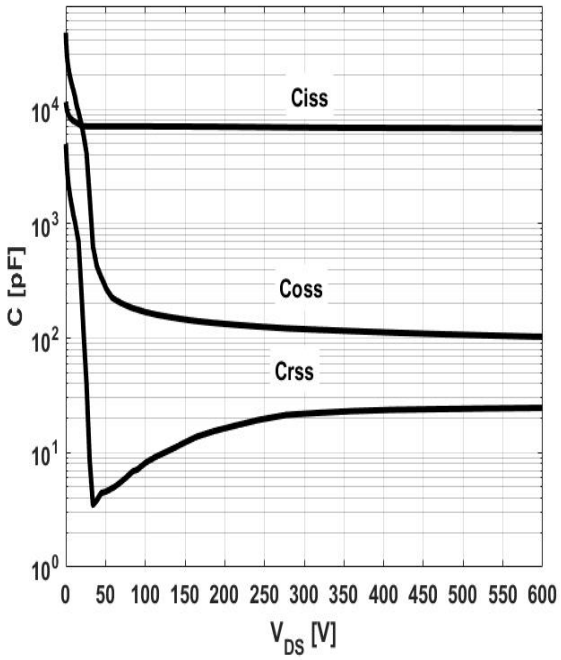
Figure 13: Drain-Source Breakdown Voltage	Figure 14: Forward Characteristics of Reverse Diode
	
$V_{BR(DSS)} = f(T_j)$; $I_D = 10mA$	$I_F = f(V_{SD})$; parameter: T_j

Figure 15: Avalanche Energy



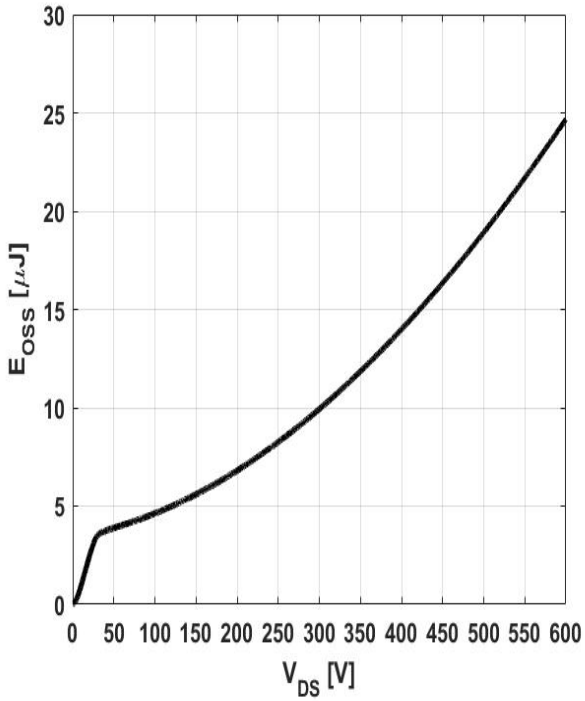
$E_{AS}=f(T_j)$; I_D=6.0A; V_{DD}=60V

Figure 16: Typ. Capacitances



$C=f(V_{DS})$; V_{GS}=0; f=1MHz

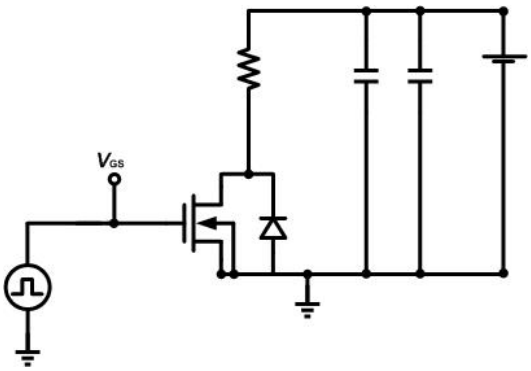
Figure 17: C_{OSS} Stored Energy

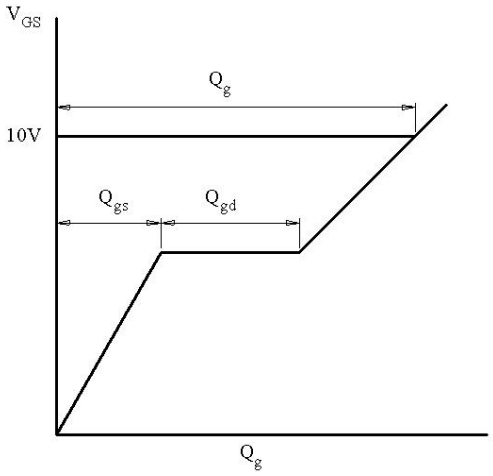


$E_{OSS}=f(V_{DS})$

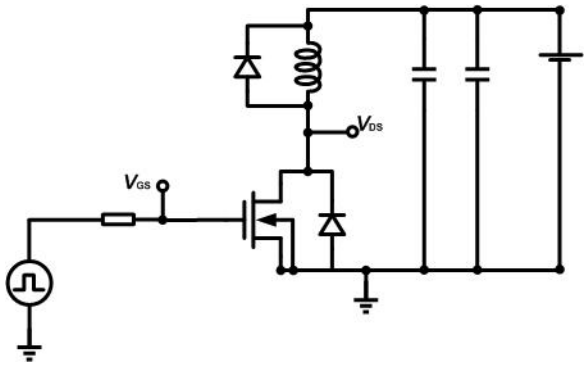
Test Circuits

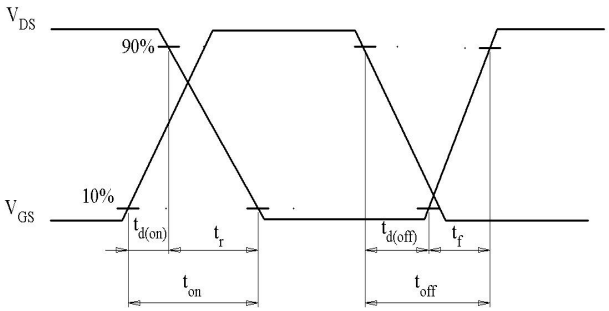
1. Gate Charge Test Circuit & Waveform



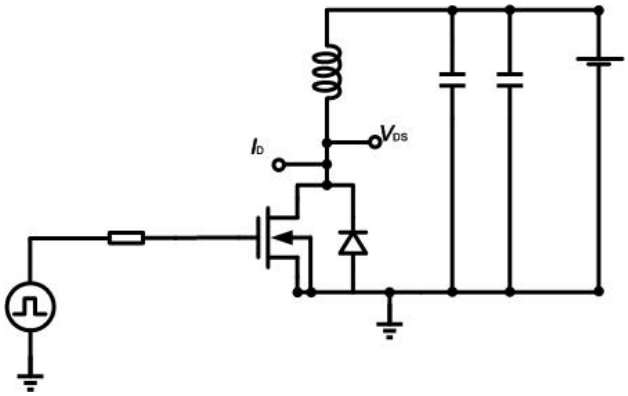


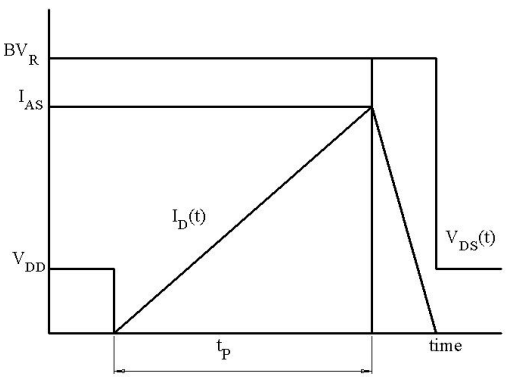
2. Switch Time Test Circuit



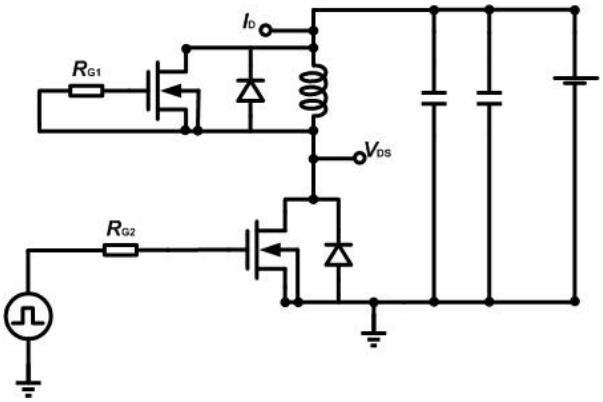


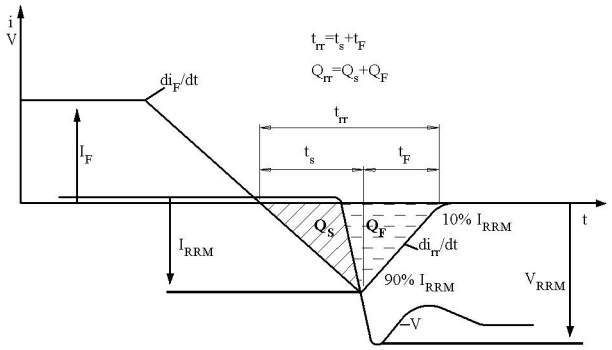
3. Unclaimed Inductive Switching Test Circuit & Waveforms





4. Test Circuit and Waveform for Diode Characteristics

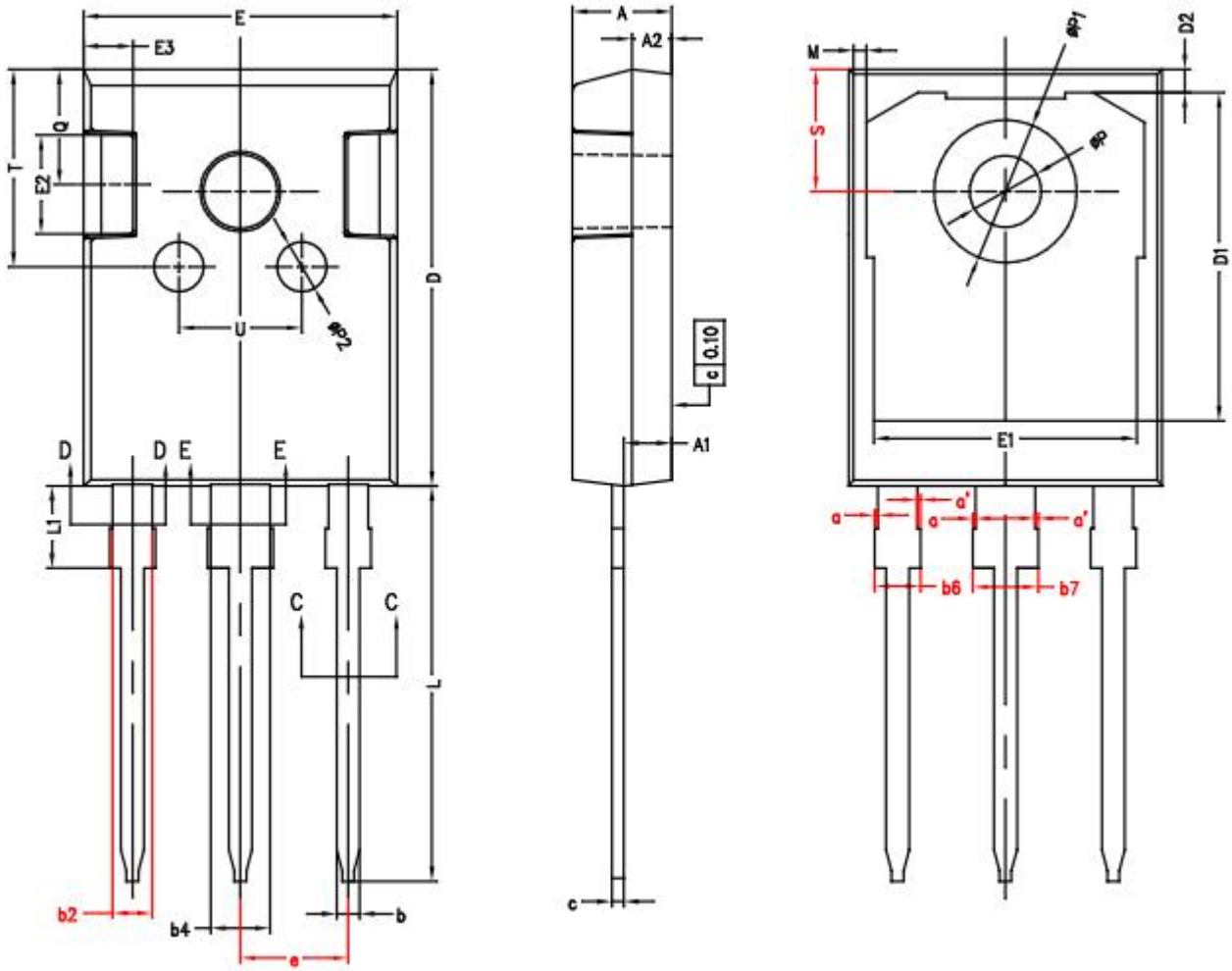




42mΩ, 650V, Super Junction N-Channel Power MOSFET SRC65R042B

Mechanical Dimensions

TO-247 **Unit: mm**



Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.90	5.00	5.10	E2	4.90	5.00	5.10
A1	2.31	2.41	2.51	E3	2.40	2.50	2.60
A2	1.90	2.00	2.10	e	5.34	5.44	5.54
b	1.12	-	1.22	L	19.80	19.92	20.10
b1	1.11	1.16	1.18	L1	3.95	4.13	4.30
b2	1.96	-	2.06	P	3.50	3.60	3.70
c	0.59	-	0.66	P1	7.00	-	7.40
D	20.90	21.00	21.10	P2	2.40	2.50	2.60
D1	16.25	16.55	16.85	Q	5.60	-	6.00
D2	1.05	1.20	1.35	S	6.05	6.15	6.25
E	15.70	15.80	15.90	T	9.80	-	10.20
E1	13.10	13.30	13.50	U	6.00	-	6.40

42mΩ, 650V, Super Junction N-Channel Power MOSFET SRC65R042B

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